

Kazutoshi Kojima

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Direct observation of dislocations propagated from 4H-SiC substrate to epitaxial layer by X-ray topography. Journal of Crystal Growth, 2004, 260, 209-216.	1.5	182
2	Effect of gate oxidation method on electrical properties of metal-oxide-semiconductor field-effect transistors fabricated on 4H-SiC C(0001 $\bar{1}$,) face. Applied Physics Letters, 2004, 84, 2088-2090.	3.3	141
3	Impact ionization coefficients of 4H silicon carbide. Applied Physics Letters, 2004, 85, 1380-1382.	3.3	115
4	Excellent effects of hydrogen postoxidation annealing on inversion channel mobility of 4H-SiC MOSFET fabricated on (1 $\bar{1}$ 2 0) face. IEEE Electron Device Letters, 2002, 23, 13-15.	3.9	94
5	Influence of growth conditions on basal plane dislocation in 4H-SiC epitaxial layer. Journal of Crystal Growth, 2004, 271, 1-7.	1.5	88
6	Dependence of acceptor levels and hole mobility on acceptor density and temperature in Al-doped p-type 4H-SiC epilayers. Journal of Applied Physics, 2004, 96, 2708-2715.	2.5	79
7	Correlation between reliability of thermal oxides and dislocations in n-type 4H-SiC epitaxial wafers. Applied Physics Letters, 2006, 89, 022909.	3.3	70
8	Epitaxial Growth of High-Quality 4H-SiC Carbon-Face by Low-Pressure Hot-Wall Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2003, 42, L637-L639.	1.5	66
9	Homoepitaxial growth of 4H-SiC on on-axis C-face substrates by chemical vapor deposition. Journal of Crystal Growth, 2004, 269, 367-376.	1.5	56
10	N-channel MOSFETs fabricated on homoepitaxy-grown 3C-SiC films. IEEE Electron Device Letters, 2003, 24, 466-468.	3.9	39
11	The Electrical Characteristics of Metal-Oxide-Semiconductor Field Effect Transistors Fabricated on Cubic Silicon Carbide. Japanese Journal of Applied Physics, 2003, 42, L625-L627.	1.5	35
12	The growth of low resistivity, heavily Al-doped 4H-SiC thick epilayers by hot-wall chemical vapor deposition. Journal of Crystal Growth, 2013, 380, 85-92.	1.5	34
13	Defect-induced performance degradation of 4H-SiC Schottky barrier diode particle detectors. Journal of Applied Physics, 2013, 113, .	2.5	32
14	Ultralow-Loss SiC Floating Junction Schottky Barrier Diodes (Super-SBDs). IEEE Transactions on Electron Devices, 2008, 55, 1954-1960.	3.0	30
15	Influence of basal-plane dislocation structures on expansion of single Shockley-type stacking faults in forward-current degradation of 4H-SiC p-n diodes. Japanese Journal of Applied Physics, 2018, 57, 04FR07.	1.5	28
16	Influence of stacking faults on the performance of 4H-SiC Schottky barrier diodes fabricated on (11 $\bar{2}$,0) face. Applied Physics Letters, 2002, 81, 2974-2976.	3.3	27
17	Development of SiC Super-Junction (SJ) Device by Deep Trench-Filling Epitaxial Growth. Materials Science Forum, 0, 740-742, 785-788.	0.3	27
18	Determination of carrier concentration by Fano interference of Raman scattering in heavily doped n-type 4H-SiC. Journal of Applied Physics, 2012, 112, .	2.5	26

#	ARTICLE	IF	CITATIONS
19	Isotropic Channel Mobility in UMOSFETs on 4H-SiC C-Face with Vicinal Off-Angle. Materials Science Forum, 0, 645-648, 999-1004.	0.3	24
20	Effect of Additional Silane on In Situ H ₂ Etching prior to 4H-SiC Homoepitaxial Growth. Materials Science Forum, 2007, 556-557, 85-88.	0.3	23
21	Development of SiC Super-Junction (SJ) Devices by Multi-Epitaxial Growth. Materials Science Forum, 0, 778-780, 845-850.	0.3	23
22	Low Resistivity, Thick Heavily Al-Doped 4H-SiC Epilayers Grown by Hot-Wall Chemical Vapor Deposition. Materials Science Forum, 0, 740-742, 181-184.	0.3	22
23	4H-SiC MOSFETs on C(000-1) Face with Inversion Channel Mobility of 127cm ² /Vs. Materials Science Forum, 2004, 457-460, 1417-1420.	0.3	21
24	Challenges of High-Performance and High-Reliability in SiC MOS Structures. Materials Science Forum, 0, 717-720, 703-708.	0.3	21
25	Strong impact of slight trench direction misalignment from $\{11\bar{1}0\}$ on deep trench filling epitaxy for SiC super-junction devices. Japanese Journal of Applied Physics, 2017, 56, 04CR05.	1.5	21
26	Effect of growth condition on micropipe filling of 4H-SiC epitaxial layer. Journal of Crystal Growth, 2005, 275, e549-e554.	1.5	20
27	Effects of Dislocations on Reliability of Thermal Oxides Grown on n-Type 4H-SiC Wafer. Materials Science Forum, 2005, 483-485, 661-664.	0.3	20
28	Determination of free carrier density in the low doping regime of 4H-SiC by Raman scattering. Applied Physics Letters, 2008, 93, .	3.3	20
29	Filling 4H-SiC trench towards selective epitaxial growth by adding HCl to CVD process. Applied Physics Express, 2015, 8, 065502.	2.4	20
30	Microstructural Analysis of Damaged Layer Introduced during Chemo-Mechanical Polishing. Materials Science Forum, 0, 778-780, 370-373.	0.3	19
31	Evaluation of 4H-SiC Thermal Oxide Reliability Using Area-Scaling Method. Japanese Journal of Applied Physics, 2009, 48, 081404.	1.5	18
32	Linear energy transfer dependence of single event gate rupture in SiC MOS capacitors. Nuclear Instruments & Methods in Physics Research B, 2014, 319, 75-78.	1.4	18
33	Filling of Deep Trench by Epitaxial SiC Growth. Materials Science Forum, 0, 740-742, 793-796.	0.3	17
34	Analysis on Generation of Localized Step-Bunchings on 4H-SiC(0001)Si Face by Synchrotron X-Ray Topography. Materials Science Forum, 0, 778-780, 398-401.	0.3	17
35	Origin analysis of expanded stacking faults by applying forward current to 4H-SiC p-n diodes. Applied Physics Express, 2017, 10, 081201.	2.4	17
36	Decrease of Charge Collection Due to Displacement Damage by Gamma Rays in a 6H-SiC Diode. IEEE Transactions on Nuclear Science, 2007, 54, 1953-1960.	2.0	16

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37	4H-SiC Homoepitaxial Growth on Substrate with Vicinal Off-Angle Lower than 1°. ECS Journal of Solid State Science and Technology, 2013, 2, N3012-N3017.	1.8	16
38	Effects of n-type 4H-SiC epitaxial wafer quality on reliability of thermal oxides. Applied Physics Letters, 2004, 85, 6182-6184.	3.3	15
39	Threshold Voltage Instability of SiC-MOSFETs on Various Crystal Faces. Materials Science Forum, 0, 778-780, 521-524.	0.3	15
40	Synchrotron X-ray topography analysis of local damage occurring during polishing of 4H-SiC wafers. Japanese Journal of Applied Physics, 2015, 54, 091301.	1.5	15
41	High-Rate Epitaxial Growth of 4H-SiC Using a Vertical-Type, Quasi-Hot-Wall CVD Reactor. Materials Science Forum, 2002, 389-393, 179-182.	0.3	14
42	Influence of C/Si Ratio on the 4H-SiC (0001) Epitaxial Growth and a Keynote for High-Rate Growth. Materials Science Forum, 2004, 457-460, 213-216.	0.3	14
43	Reducing Stacking Faults in Highly Doped N-Type 4H-SiC Crystal. Materials Science Forum, 0, 679-680, 8-11.	0.3	14
44	Numerical analysis of the Gibbs-Thomson effect on trench-filling epitaxial growth of 4H-SiC. Applied Physics Express, 2016, 9, 035601.	2.4	14
45	An empirical growth window concerning the input ratio of HCl/SiH ₄ gases in filling 4H-SiC trench by CVD. Applied Physics Express, 2017, 10, 055505.	2.4	14
46	Growth of silicon carbide epitaxial layers on 150-mm-diameter wafers using a horizontal hot-wall chemical vapor deposition. Journal of Crystal Growth, 2013, 381, 139-143.	1.5	13
47	Epitaxial growth and characterization of thick multi-layer 4H-SiC for very high-voltage insulated gate bipolar transistors. Journal of Applied Physics, 2015, 118, .	2.5	13
48	Modeling of SiC-CVD on Si-face/C-face in a horizontal hot-wall reactor. Journal of Crystal Growth, 2005, 275, e515-e520.	1.5	12
49	Fabrication of 4H-SiC Floating Junction Schottky Barrier Diodes (Super-SBDs) and their Electrical Properties. Materials Science Forum, 2006, 527-529, 1175-1178.	0.3	12
50	Nitrogen incorporation characteristics on a 4H-SiC epitaxial layer. Applied Physics Letters, 2006, 88, 021907.	3.3	12
51	Transient Analysis of an Extended Drift Region in a 6H-SiC Diode Formed by a Single Alpha Particle Strike and Its Contribution to the Increased Charge Collection. IEEE Transactions on Nuclear Science, 2011, 58, 305-313.	2.0	12
52	$E_{1/2}$ traps in 6H-SiC studied with Laplace deep level transient spectroscopy. Applied Physics Letters, 2013, 102, .	3.3	12
53	Hopping conduction range of heavily Al-doped 4H-SiC thick epilayers grown by CVD. Applied Physics Express, 2015, 8, 121302.	2.4	12
54	Systematic investigation on in-plane anisotropy of surface and buried channel mobility of metal-oxide-semiconductor field-effect-transistors on Si-, a-, and m-face 4H-SiC. Applied Physics Letters, 2015, 106, .	3.3	12

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55	Thermometric quantum sensor using excited state of silicon vacancy centers in 4H-SiC devices. Applied Physics Letters, 2021, 118, .	3.3	12
56	Significant Improvement of Inversion Channel Mobility in 4H-SiC MOSFET on (11-20) Face Using Hydrogen Post-Oxidation Annealing. Materials Science Forum, 2002, 389-393, 1061-1064.	0.3	11
57	Reverse characteristics of pn diodes on 4H-SiC(000-1) C and (11-20) face. Applied Physics Letters, 2004, 84, 1774-1776.	3.3	11
58	Influence of lattice polarity of nitrogen and aluminum doping on 4H-SiC epitaxial layer. Microelectronic Engineering, 2006, 83, 79-81.	2.4	11
59	Epitaxial Growth of Thick Multi-Layer 4H-SiC for the Fabrication of Very High-Voltage C-Face n-Channel IGBT. Materials Science Forum, 0, 778-780, 135-138.	0.3	11
60	Effects of Pyrogenic Reoxidation Annealing on Inversion Channel Mobility of 4H-SiC Metal-Oxide-Semiconductor Field-Effect Transistor Fabricated on $(11\bar{1}2)0$ Face. Japanese Journal of Applied Physics, 2001, 40, L1201-L1203.	1.5	10
61	Ammonia-free high temperature metalorganic vapor phase epitaxy (AFHT-MOVPE): a new approach to high quality AlN growth. CrystEngComm, 2018, 20, 7364-7370.	2.6	10
62	Control of the Surface Morphology on Low Off Angled 4H-SiC Homoepitaxial Growth. Materials Science Forum, 0, 615-617, 113-116.	0.3	9
63	Carrier Density Dependence of Fano Type Interference in Raman Spectra of p-type 4H-SiC. Materials Science Forum, 0, 778-780, 475-478.	0.3	9
64	Suppression of short step bunching generated on 4H-SiC Si-face substrates with vicinal off-angle. Journal of Crystal Growth, 2014, 401, 673-676.	1.5	9
65	Experiment on alleviating the bending of CVD-grown heavily Al-doped 4H-SiC epiwafer by codoping of N. Japanese Journal of Applied Physics, 2015, 54, 04DP08.	1.5	9
66	Development of 4H-SiC Schottky np diode with high blocking voltage and ultralow on-resistance. Applied Physics Letters, 2020, 116, .	3.3	9
67	Investigation of Residual Impurities in 4H-SiC Epitaxial Layers Grown by Hot-Wall Chemical Vapor Deposition. Materials Science Forum, 2002, 389-393, 215-218.	0.3	8
68	Homoepitaxial Growth on a 4H-SiC C-Face Substrate. Chemical Vapor Deposition, 2006, 12, 489-494.	1.3	8
69	Investigation of In-Grown Dislocations in 4H-SiC Epitaxial Layers. Materials Science Forum, 2006, 527-529, 147-152.	0.3	8
70	High Inversion Channel Mobility of 4H-SiC MOSFETs Fabricated on C(000-1) Epitaxial Substrate with Vicinal (Below $1\bar{1}^\circ$) Off-Angle. Materials Science Forum, 2006, 527-529, 1043-1046.	0.3	8
71	Simulation, Fabrication and Characterization of 4H-SiC Floating Junction Schottky Barrier Diodes (Super-SBDs). Materials Science Forum, 2007, 556-557, 881-884.	0.3	8
72	Doping Concentration Optimization for Ultra-Low-Loss 4H-SiC Floating Junction Schottky Barrier Diode (Super-SBD). Materials Science Forum, 2009, 615-617, 655-658.	0.3	8

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73	4H-SiC Homoepitaxial Growth on Vicinal-Off Angled Si-Face Substrate. Materials Science Forum, 0, 645-648, 99-102.	0.3	8
74	Effect of Post-Oxidation Annealing in Wet O ₂ and N ₂ O Ambient on Thermally Grown SiO ₂ /4H-SiC Interface for P-Channel MOS Devices. Materials Science Forum, 0, 717-720, 709-712.	0.3	8
75	Influence of growth pressure on filling 4H-SiC trenches by CVD method. Japanese Journal of Applied Physics, 2016, 55, 01AC04.	1.5	8
76	Nondestructive measurements of depth distribution of carrier lifetimes in 4H-SiC thick epitaxial layers using time-resolved free carrier absorption with intersectional lights. Review of Scientific Instruments, 2020, 91, 123902.	1.3	8
77	Impact Ionization Coefficients of 4H-SiC. Materials Science Forum, 2004, 457-460, 673-676.	0.3	7
78	2-Inch 4H-SiC Homoepitaxial Layer Grown on On-Axis C-Face Substrate by CVD Method. Materials Science Forum, 2005, 483-485, 93-96.	0.3	7
79	Charge Collection Properties of 6H-SiC Diodes by Wide Variety of Charged Particles up to Several Hundreds MeV. Materials Science Forum, 2009, 615-617, 861-864.	0.3	7
80	Charge Collection Efficiency of 6H-SiC P ⁺ /N Diodes Degraded by Low-Energy Electron Irradiation. Materials Science Forum, 0, 645-648, 921-924.	0.3	7
81	The Growth of 3-Inch 4H-SiC Si-Face Epitaxial Wafer with Vicinal Off-Angle. Materials Science Forum, 0, 740-742, 193-196.	0.3	7
82	Suppression of 3C-Inclusion Formation during Growth of 4H-SiC Si-Face Homoepitaxial Layers with a 1° Off-Angle. Materials, 2014, 7, 7010-7021.	2.9	7
83	Observation of carrier lifetime distribution in 4H-SiC thick epilayers using microscopic time-resolved free carrier absorption system. Journal of Applied Physics, 2020, 128, 105702.	2.5	7
84	Homoepitaxial growth and investigation of stacking faults of 4H-SiC C-face epitaxial layers with a 1° off-angle. Japanese Journal of Applied Physics, 2015, 54, 04DP04.	1.5	7
85	A Large Reduction in Interface-State Density for MOS Capacitor on 4H-SiC (11-2 0) Face Using H ₂ and H ₂ O Vapor Atmosphere Post-Oxidation Annealing. Materials Science Forum, 2002, 389-393, 1057-1060.	0.3	6
86	Uniformity of 4H-SiC epitaxial layers grown on 3-in diameter substrates. Journal of Crystal Growth, 2003, 258, 113-122.	1.5	6
87	Charge Enhancement Effects in 6H-SiC MOSFETs Induced by Heavy Ion Strike. IEEE Transactions on Nuclear Science, 2010, , .	2.0	6
88	Improvement of Homoepitaxial Layer Quality Grown on 4H-SiC Si-Face Substrate Lower than 1 Degree Off Angle. Materials Science Forum, 0, 717-720, 141-144.	0.3	6
89	Electrical Properties of MOS Structures on 4H-SiC (11-20) Face. Materials Science Forum, 2013, 740-742, 621-624.	0.3	6
90	Epitaxial Growth of (11-20) 4H-SiC Using Substrate Grown in the [11-20] Direction. Materials Science Forum, 2002, 389-393, 195-198.	0.3	5

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91	Replication of Defects from 4H-SiC Wafer to Epitaxial Layer. Materials Science Forum, 2002, 389-393, 447-450.	0.3	5
92	Transient Currents Induced in 6H-SiC MOS Capacitors by Oxygen Ion Incidence. Materials Science Forum, 0, 615-617, 517-520.	0.3	5
93	Homo-Epitaxial Growth on 2Å° Off-Cut 4H-SiC(0001) Si-Face Substrates Using H ₂ -SiH ₄ -C ₃ H ₈ CVD System. Materials Science Forum, 2014, 778-780, 214-217.	0.3	5
94	Development of diagnostic method for deep levels in semiconductors using charge induced by heavy ion microbeams. Nuclear Instruments & Methods in Physics Research B, 2015, 348, 240-245.	1.4	5
95	Electrical and physical characterizations of the effects of oxynitridation and wet oxidation at the interface of SiO ₂ /4H-SiC(0001) and. Japanese Journal of Applied Physics, 2016, 55, 04ER19.	1.5	5
96	Study of spiral growth on 4H-silicon carbide on-axis substrates. Journal of Crystal Growth, 2017, 475, 251-255.	1.5	5
97	Control of Surface Morphologies for Epitaxial Growth on Low Off-Angle 4H-SiC (0001) Substrates. Materials Science Forum, 2001, 353-356, 135-138.	0.3	4
98	A Long-Term Reliability of Thermal Oxides Grown on n-Type 4H-SiC Wafer. Materials Science Forum, 2004, 457-460, 1269-1274.	0.3	4
99	Single-Alpha-Particle-Induced Charge Transient Spectroscopy of the 6H-SiC p^+n Diode Irradiated With High-Energy Electrons. IEEE Transactions on Nuclear Science, 2011, 58, 3328-3332.	2.0	4
100	Conversion of Basal Plane Dislocations to Threading Edge Dislocations in Growth of Epitaxial Layers on 4H-SiC Substrates with a Vicinal Off-Angle. Materials Science Forum, 0, 778-780, 99-102.	0.3	4
101	C-Face Epitaxial Growth of 4H-SiC on Quasi-150-mm Diameter Wafers with High Throughput. Materials Science Forum, 0, 778-780, 109-112.	0.3	4
102	Characterization of stacking faults with emission wavelengths of over 500 nm formed in 4H-SiC epitaxial films. Journal of Crystal Growth, 2017, 476, 99-106.	1.5	4
103	Reduction of background carrier concentration and lifetime improvement for 4H-SiC C-face epitaxial growth. Japanese Journal of Applied Physics, 2017, 56, 081302.	1.5	4
104	Carrier dynamics of silicon vacancies of SiC under simultaneous optically and electrically excitations. Applied Physics Letters, 2021, 118, .	3.3	4
105	SiC p+n Junction Diodes Toward Beam Monitor Applications. IEEE Transactions on Nuclear Science, 2021, 68, 2787-2793.	2.0	4
106	Electrical Properties of pn Diodes on 4H-SiC(000-1) C-Face and (11-20) Face. Materials Science Forum, 2004, 457-460, 1065-1068.	0.3	3
107	Epitaxial Overgrowth of 4H-SiC for Devices with p-Buried Floating Junction Structure. Materials Science Forum, 2005, 483-485, 147-150.	0.3	3
108	Lifetime Control of the Minority Carrier in PiN Diodes by He ⁺ Ion Implantation. Materials Science Forum, 2005, 483-485, 985-988.	0.3	3

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109	Gate-Area Dependence of SiC Thermal Oxides Reliability. Materials Science Forum, 0, 600-603, 787-790.	0.3	3
110	Characterization of Electrical Properties in SiC Crystals by Raman Scattering Spectroscopy. Materials Science Forum, 2008, 600-603, 501-504.	0.3	3
111	Characterization of the Defect Evolution in Thick Heavily Al-Doped 4H-SiC Epilayers. Materials Science Forum, 2014, 778-780, 151-154.	0.3	3
112	4H-SiC Carbon-Face Epitaxial Layers Grown by Low-Pressure Hot-Wall Chemical Vapor Deposition. Materials Science Forum, 2004, 457-460, 209-212.	0.3	2
113	Relationship between the Current Direction in the Inversion Layer and the Electrical Characteristics of Metal-Oxide-Semiconductor Field Effect Transistors on 3C-SiC. Materials Science Forum, 2004, 457-460, 1405-1408.	0.3	2
114	Effect of Surface Orientation and Off-Angle on Surface Roughness and Electrical Properties of p-Type Impurity Implanted 4H-SiC Substrate after High Temperature Annealing. Materials Science Forum, 2006, 527-529, 835-838.	0.3	2
115	Oxygen Ion Induced Charge in SiC MOS Capacitors Irradiated with Gamma-Rays. Materials Science Forum, 2011, 679-680, 362-365.	0.3	2
116	Development of Homoepitaxial Growth Technique on 4H-SiC Vicinal Off Angled Substrate. Materials Science Forum, 2014, 778-780, 125-130.	0.3	2
117	Suppressing Al memory effect on CVD growth of 4H-SiC epilayers by adding hydrogen chloride gas. Japanese Journal of Applied Physics, 2014, 53, 04EP07.	1.5	2
118	Investigation of Factors Influencing the Occurrence of 3C-Inclusions for the Thick Growth of on-Axis C-Face 4H-SiC Epitaxial Layers. Materials, 2020, 13, 4818.	2.9	2
119	Influence of the Crystalline Quality of Epitaxial Layers on Inversion Channel Mobility in 4H-SiC MOSFETs. Materials Science Forum, 2002, 389-393, 1053-1056.	0.3	1
120	Influence of Micropipe and Domain Boundary in SiC Substrate on the DC Characteristics of AlGaN/GaN HFET. Materials Science Forum, 2007, 556-557, 1043-1046.	0.3	1
121	Transient Response to High Energy Heavy Ions in 6H-SiC n ⁺ /p Diodes. Materials Science Forum, 0, 600-603, 1039-1042.	0.3	1
122	Effects of Fabrication Process on the Electrical Characteristics of n-Channel MOSFETs Irradiated with Gamma-Rays. Materials Science Forum, 2008, 600-603, 707-710.	0.3	1
123	Peak Degradation of Heavy-Ion Induced Transient Currents in 6H-SiC MOS Capacitors. Materials Science Forum, 0, 717-720, 469-472.	0.3	1
124	Reducing the Wafer Off Angle for 4H-SiC Homoepitaxy. ECS Transactions, 2013, 58, 111-117.	0.5	1
125	Suppression of Al Memory-Effect on Growing 4H-SiC Epilayers by Hot-Wall Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2013, 52, 04CP04.	1.5	1
126	Investigation of Low Off-Angled 4H-SiC Epitaxial Wafers for Power Device Applications. ECS Journal of Solid State Science and Technology, 2017, 6, P547-P552.	1.8	1

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127	Effects of Steam Annealing on Electrical Characteristics of 3C-SiC Metal-Oxide-Semiconductor Structures. Materials Science Forum, 2000, 338-342, 1129-1132.	0.3	0
128	Distribution Profile of Deep Levels in SiC Observed by Isothermal Capacitance Transient Spectroscopy. Materials Science Forum, 2002, 389-393, 851-854.	0.3	0
129	Defect Characterization of 4H-SiC Bulk Crystals Grown on Micropipe Filled Seed Crystals. Materials Science Forum, 2005, 483-485, 315-318.	0.3	0
130	Challenges of 4H-SiC MOSFETs on the C(000-1) Face toward the Achievement of Ultra Low On-Resistance. Materials Science Forum, 0, 600-603, 907-912.	0.3	0
131	Defects in an Electron-Irradiated 6H-SiC Diode Studied by Alpha Particle Induced Charge Transient Spectroscopy: Their Impact on the Degraded Charge Collection Efficiency. Materials Science Forum, 0, 717-720, 267-270.	0.3	0
132	Effects of radiation-induced defects on the charge collection efficiency of a silicon carbide particle detector. , 2013, , .		0
133	Breakdown voltage in silicon carbide metal-oxide-semiconductor devices induced by ion beams. , 2013, , .		0
134	Dependence of the Growth Parameters on the In-Plane Distribution of 150 mm Ĩ† Size SiC Epitaxial Wafer. Materials Science Forum, 2014, 778-780, 139-142.	0.3	0